

## NCE P-Channel Enhancement Mode Power MOSFET

## **Description**

The NCE2303 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , This device is suitable for use as a load switch or in PWM applications.

#### **General Features**

•  $V_{DS} = -30V, I_{D} = -2.0A$ 

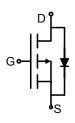
 $R_{DS(ON)}$  < 130m $\Omega$  @  $V_{GS}$ =-10V

 $R_{DS(ON)}$  < 180m $\Omega$  @  $V_{GS}$ =-4.5V

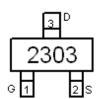
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

## **Application**

- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOT-23 top view

### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
2303	NCE2303	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (T<sub>A</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	-30	V	
Gate-Source Voltage	V <sub>GS</sub>	±20	V	
Drain Current-Continuous	I <sub>D</sub>	-2.0	Α	
Drain Current-Pulsed (Note 1)	I <sub>DM</sub>	-10	Α	
Maximum Power Dissipation	P <sub>D</sub>	1.0	W	
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 150	°C	

## **Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ hetaJA}$	125	°C/W

### Electrical Characteristics (T<sub>A</sub>=25°Cunless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-30	-33	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V,V <sub>GS</sub> =0V	-	-	-1	μΑ



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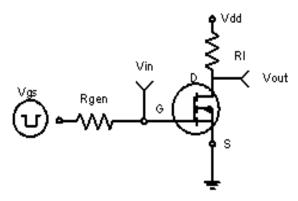
# NCE2303

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250μA	-1	-1.6	-2.5	V	
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-2.0A	-	72	130	mΩ	
Diam-Source On-State Resistance		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-1.5A	-	110	180	mΩ	
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =-10V,I <sub>D</sub> =-2A		2	-	S	
Dynamic Characteristics (Note4)							
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =-15V.V <sub>GS</sub> =0V.	-	226	-	PF	
Output Capacitance	Coss	F=1.0MHz	-	47	-	PF	
Reverse Transfer Capacitance	C <sub>rss</sub>	F-1.UIVITZ	-	28	-	PF	
Switching Characteristics (Note 4)							
Turn-on Delay Time	t <sub>d(on)</sub>		-	9	-	nS	
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =-15V, $R_L$ =15 $\Omega$	-	9	-	nS	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =-10V, $R_{GEN}$ =6 $\Omega$	-	18	-	nS	
Turn-Off Fall Time	t <sub>f</sub>		-	6	-	nS	
Total Gate Charge	Qg		-	8.5	-	nC	
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-15V,I <sub>D</sub> =-2.0A,V <sub>GS</sub> =-10V	-	2.3	-	nC	
Gate-Drain Charge	$Q_{gd}$	]	-	1.5	-	nC	
Drain-Source Diode Characteristics						•	
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =-2.0A	-	-	-1.2	V	

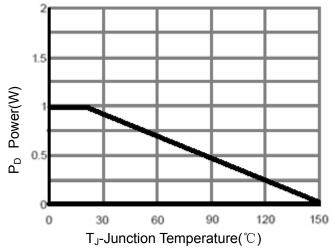
### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production

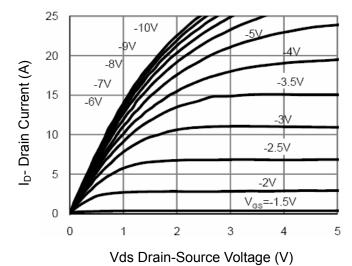
## **Typical Electrical and Thermal Characteristics**



**Figure 1:Switching Test Circuit** 



**Figure 3 Power Dissipation** 



**Figure 5 Output Characteristics** 

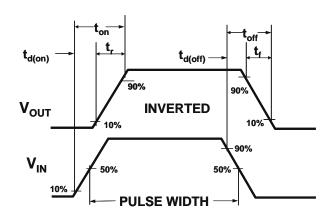


Figure 2:Switching Waveforms

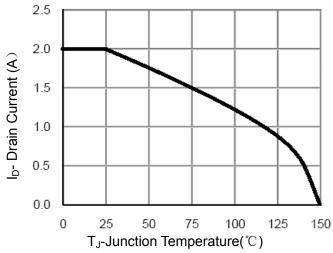


Figure 4 Drain Current

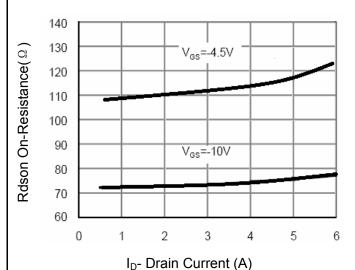
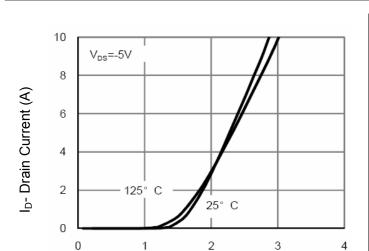
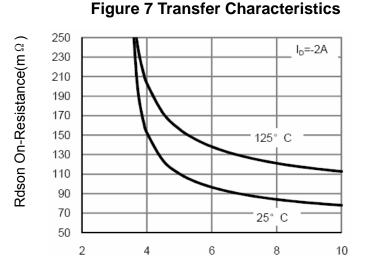


Figure 6 Drain-Source On-Resistance



Vgs Gate-Source Voltage (V)



Vgs Gate-Source Voltage (V)

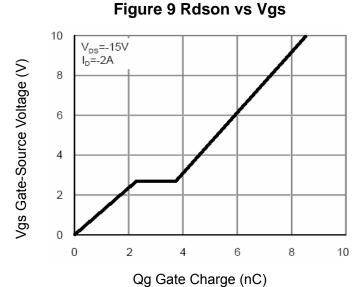
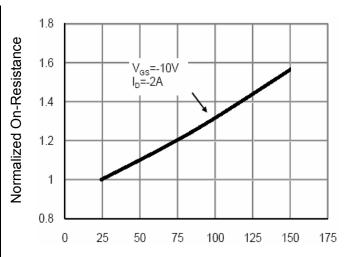
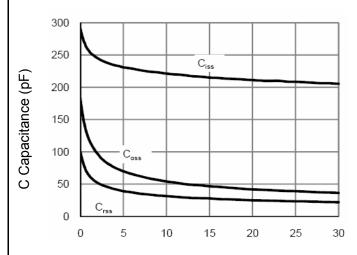


Figure 11 Gate Charge



T<sub>J</sub>-Junction Temperature(℃)

Figure 8 Drain-Source On-Resistance



Vds Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds

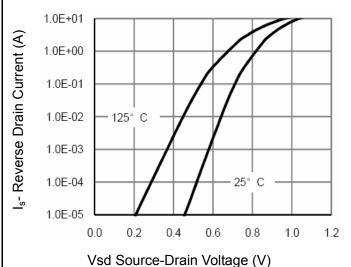
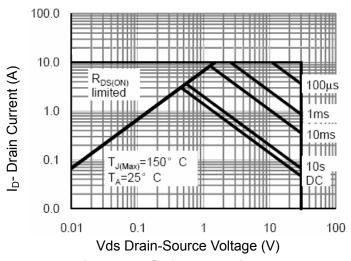
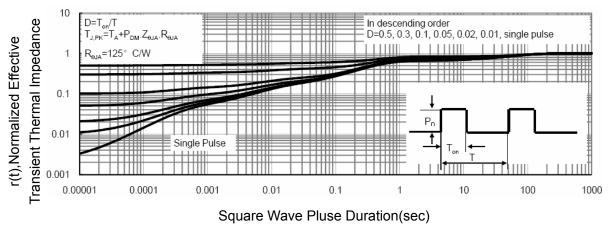


Figure 12 Source- Drain Diode Forward

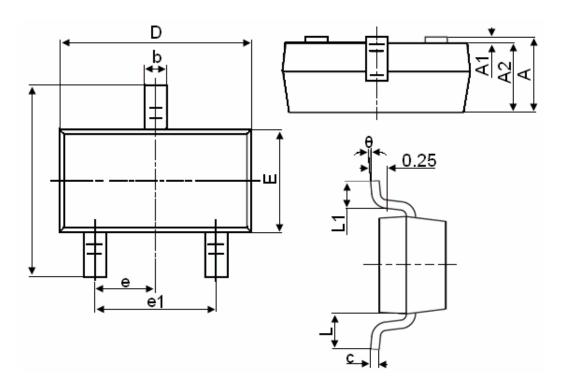


**Figure 13 Safe Operation Area** 



**Figure 14 Normalized Maximum Transient Thermal Impedance** 

# **SOT-23 Package Information**



Symbol	Dimensions in Millimeters				
Symbol	MIN.	MAX.			
Α	0.900	1.150			
A1	0.000	0.100			
A2	0.900	1.050			
b	0.300	0.500			
С	0.080	0.150			
D	2.800	3.000			
E	1.200	1.400			
E1	2.250	2.550			
е		0.950TYP			
e1	1.800	2.000			
L	0.550REF				
L1	0.300	0.500			
θ	0°	8°			

### Notes

- 1. All dimensions are in millimeters.
- 2. Tolerance  $\pm 0.10$ mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- 5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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NCE2303

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